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Chen et al.(10) **Pub. No.: US 2024/0223133 A1**(43) **Pub. Date: Jul. 4, 2024**(54) **RADIO-FREQUENCY CIRCUIT AND BIAS CIRCUIT**(71) Applicant: **RichWave Technology Corp.**, Taipei City (TW)(72) Inventors: **Chang-Heng Chen**, Taipei City (TW);
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(57)

ABSTRACT

A radio-frequency circuit can include a power amplifier, a first bias circuit and a second bias circuit. The power amplifier can include an input terminal used to receive a radio-frequency signal, and an output terminal used to output an amplified radio-frequency signal. The first bias circuit can include a first output terminal coupled to the input terminal of the power amplifier through a common node. The second bias circuit can include a second output terminal and a current adjustment circuit, where the second output terminal can be coupled to the common node, and the current adjustment circuit can include a transistor. The transistor can include a first terminal coupled to the second output terminal, a second terminal used to receive a reference voltage, and a control terminal.

